

SB3200 SCHOTTKY RECTIFIER

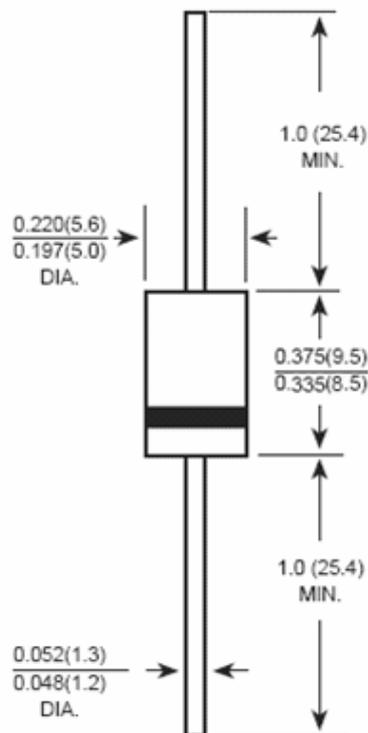
Applications:

- Switching power supply
- Converters
- Free-Wheeling diodes
- Reverse battery protection
- Disk drives
- Battery charging

Features:

- Schottky Barrier Chip
- Guard Ring Die Construction for Transient Protection
- High Current Capability
- Low Power Loss, High Efficiency
- High Surge Current Capability
- For Use in Low Voltage, High Frequency Inverters, Free Wheeling, and Polarity Protection Applications
- This is a Pb – Free Device
- All SMC parts are traceable to the wafer lot
- Additional testing can be offered upon request

Mechanical Dimensions: In Inches / mm



DO-201AD



Marking Diagram:



Where XXXXX is YYWWL

- SB = Device Type
- 3 = Forward Current (3A)
- 200 = Reverse Voltage (200V)
- SSG = SSG
- YY = Year
- WW = Week
- L = Lot Number

Cautions : Molding resin
Epoxy resin UL:94V-0

Ordering Information:

Device	Package	Shipping
SB3200	DO-201AD (Pb-Free)	1250 pcs / Tape

For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification.



Maximum Ratings and Electrical Characteristics @ $T_A=25^\circ\text{C}$ unless otherwise specified

Single Phase, half wave, 60Hz, resistive or inductive load.
For capacitive load, derate current by 20%.

Characteristic	Symbol	SB3200	Unit
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	V_{RRM} V_{RWM} V_R	200	V
Average Rectified Output Current (Note 1) @ $T_A = 105^\circ\text{C}$	I_o	3.0	A
Non-Repetitive Peak Forward Surge Current 8.3ms Single half sine-wave superimposed on rated load (JEDEC Method)	I_{FSM}	110	A
Forward Voltage @ $I_F = 3.0\text{A}$	V_{FM}	0.90	V
Peak Reverse Current At Rated DC Blocking Voltage @ $T_A = 25^\circ\text{C}$ @ $T_A = 125^\circ\text{C}$	I_{RM}	1.0 6.0	mA
Typical Junction Capacitance (Note 2)	C_j	150	pF
Max. Voltage Rate of Change	dv/dt	10,000	V/ μs
Storage Temperature Range	T_{STG}	-55 to +150	$^\circ\text{C}$
Max. Junction Temperature	T_J	-55 to +150	$^\circ\text{C}$
Approximate Weight	wt	1.02	g
Case Style	DO-201AD		

Note:1. Leads maintained at ambient temperature at a distance of 9.5mm from the case.

2. Measured at 1.0 MHz and applied reverse voltage of 4.0V D.C.

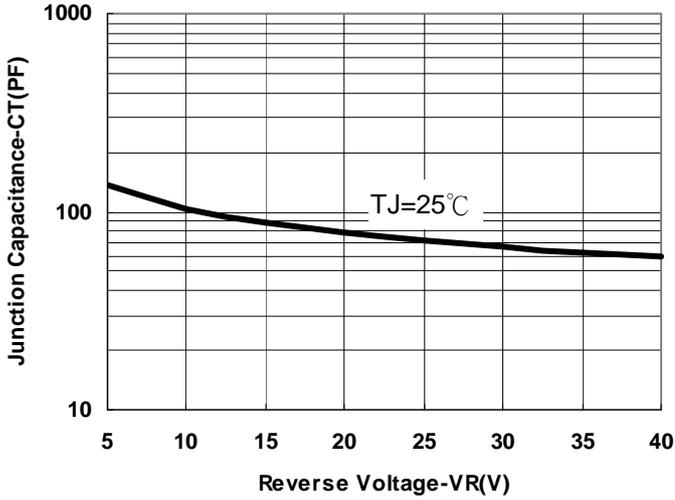


Fig.1-Typical Junction Capacitance Vs.Reverse Voltage

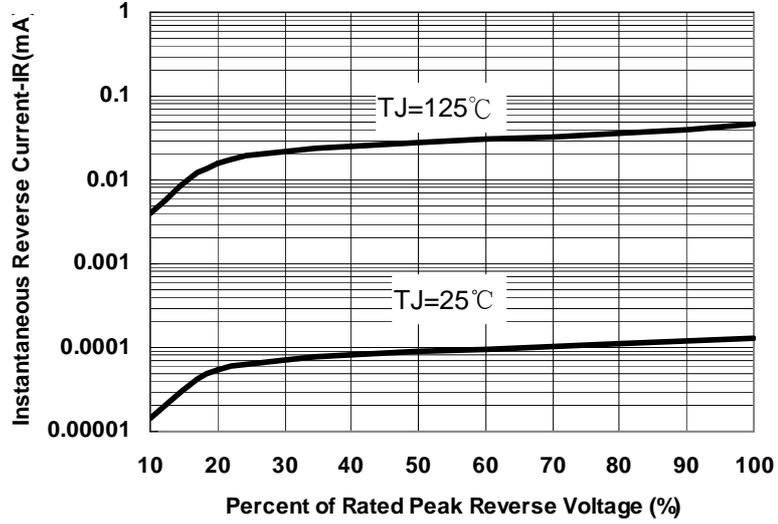


Fig.2-Typical Values Of Reverse Current Vs.Reverse Voltage

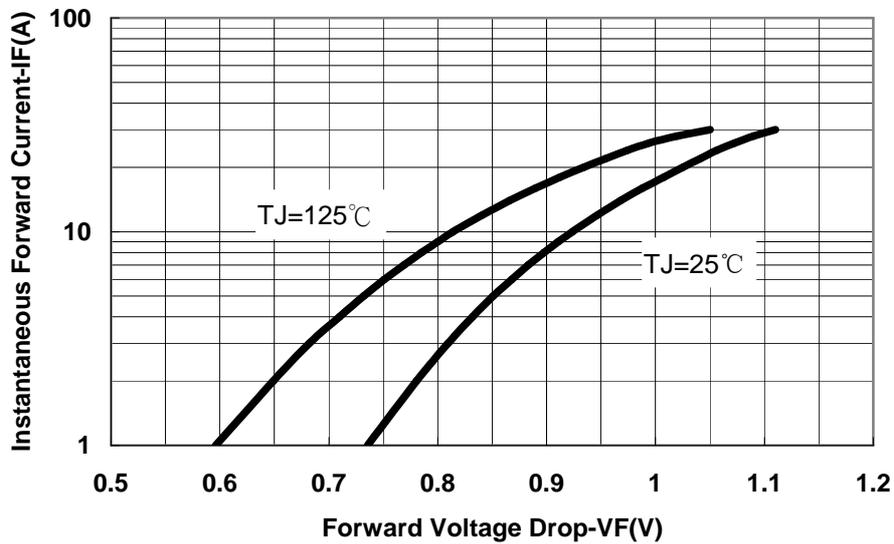


Fig.3-Typical Forward Voltage Drop Characteristics



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